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		Complete if Known	
		<b>Application Number</b> 08/903453	
		<b>Filing Date</b> July 29, 1997	
		<b>First Named Inventor</b> Forbes, Leonard	
		<b>Group Art Unit</b> 2815	
<b>Examiner Name</b> Eckert II, George			
Sheet 1 of 1		Attorney Docket No: 00303.378US1	

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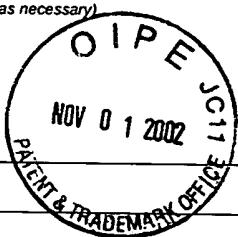
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Sheet 1 of 1

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